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Patent

Attorney's Docket No. 030682-066  
NOV 14 2001

TECHNOLOGY CENTER 2800

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of )  
Atsushi MIYANISHI et al. ) Group Art Unit: 2815  
Application No.: 09/114,203 ) Examiner: B. Baumeister  
Filed: July 13, 1998 )  
For: SEMICONDUCTOR DEVICE )  
)  
)  
)  
)

**AMENDMENT/REPLY TRANSMITTAL LETTER**

Assistant Commissioner for Patents  
Washington, D.C. 20231

Date: November 9, 2001

Sir:

Enclosed is a reply for the above-identified patent application.

- [X] A Petition for Extension of Time is also enclosed.
- [ ] A Terminal Disclaimer and a check for [ ] \$55.00 (248) [ ] \$110.00 (148) to cover the requisite Government fee are also enclosed.
- [ ] Also enclosed is \_\_\_\_\_.
- [ ] Small entity status is hereby claimed.
- [ ] Applicant(s) request continued examination under 37 C.F.R. § 1.114 and enclose the [ ] \$370.00 (279) [ ] \$740.00 (179) fee due under 37 C.F.R. § 1.17(e).
- [ ] Applicant(s) previously submitted \_\_\_, on \_\_\_, for which continued examination is requested.
- [ ] Applicant(s) request suspension of action by the Office until at least \_\_\_, which does not exceed three months from the filing of this RCE, in accordance with 37 C.F.R. § 1.103(c). The required fee under 37 C.F.R. § 1.17(i) is enclosed.
- [ ] A Request for Entry and Consideration of Submission under 37 C.F.R. § 1.129(a) (146/246) is also enclosed.
- [X] No additional claim fee is required.

[ ] An additional claim fee is required, and is calculated as shown below:

AMENDED CLAIMS					
	NO. OF CLAIMS	HIGHEST NO. OF CLAIMS PREVIOUSLY PAID FOR	EXTRA CLAIMS	RATE	ADDT'L FEE
Total Claims	12	MINUS 20 =	0	× \$18.00 (103) =	0.00
Independent Claims	4	MINUS 4 =	0	× \$80.00 (102) =	0.00
If Amendment adds multiple dependent claims, add \$270.00 (104)					
Total Amendment Fee					
If small entity status is claimed, subtract 50% of Total Amendment Fee					
<b>TOTAL ADDITIONAL FEE DUE FOR THIS AMENDMENT</b>					

[ ] A claim fee in the amount of \$ \_\_\_\_\_ is enclosed.

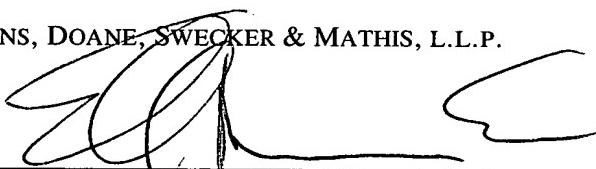
[ ] Charge \$ \_\_\_\_\_ to Deposit Account No. 02-4800.

The Commissioner is hereby authorized to charge any appropriate fees under 37 C.F.R. §§ 1.16, 1.17, 1.20(d) and 1.21 that may be required by this paper, and to credit any overpayment, to Deposit Account No. 02-4800. This paper is submitted in duplicate.

Respectfully submitted,

BURNS, DOANE, SWECKER & MATHIS, L.L.P.

By:

  
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Date: November 9, 2001

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In re Patent Application of

Atsushi MIYANISHI et al.

Application No.: 09/114,203

Filed: July 13, 1998

For: SEMICONDUCTOR DEVICE



Group Art Unit: 2815

Examiner: B. Baumeister

#20

11-20-01

T. Flowers

**RESPONSE UNDER 37 C.F.R. §1.116**

Assistant Commissioner for Patents  
Washington, D.C. 20231

Date: November 9, 2001

Sir:

This response responds to the Office Action dated July 10, 2001 (Paper No. 18).

Concurrently filed with this response is a Petition for Extension of Time for one month.

**REMARKS**

This response responds to the Office Action dated July 10, 2001, in which the Examiner rejected claims 1 and 12 under 35 U.S.C. § 103.

Claim 1 claims a semiconductor device comprising an active area and an insulating film. The active area is provided with at least one MOS transistor. The insulating film defines the active area. The active area is set in a shape having a concave part in a shape along a plan view. The active area is provided with an ordinary region and a depressed region having an edge portion which is depressed beyond the ordinary region due to the presence of the concave part. The at least one MOS transistor includes first and second MOS transistors. The first MOS transistor is formed in the depressed region. The second MOS transistor is formed on the ordinary region. A length of a margin part of a first gate